

## M54HCT374 M74HCT374

# OCTAL D-TYPE FLIP-FLOP WITH 3-STATE OUTPUT

- LOW POWER DISSIPATION I<sub>CC</sub> = 4 μA (MAX.) at T<sub>A</sub> = 25°C
- COMPATIBLE WITH TTL OUTPUTS V<sub>IH</sub> = 2 V (MIN) V<sub>IL</sub> = 0.8 V (MAX.)
- OUTPUT DRIVE CAPABILITY 15 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE |IOH| = IOL = 6 mA (MIN.)
- BALANCED PROPAGATION DELAYS
  tpi H = tpHi
- PIN AND FUNCTION COMPATIBLE WITH 54/74LS374

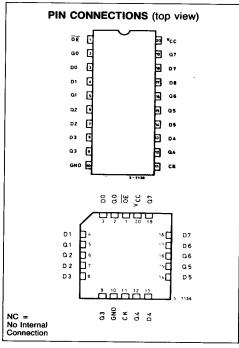
# B1N F1 Plastic Package Ceramic Frit Seal Package M1 C1 Micro Package Plastic Chip Carrier ORDERING NUMBERS: M54HCT374 F1 M74HCT374 C1 M74HCT374 B1N M74HCT374 M1

# The M54/74HC

The M54/74HCT374 is a high speed CMOS OCTAL D-TYPE FLIP-FLOP WITH 3-STATE OUTPUT fabricated in silicon gate C2MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption. This 8-bit D-type flip-flop is controlled by a clock input (CK) and an output enable input (OE). On the positive transition of the clock, the Q outputs will be set precisely to the logic state that was setup at the D inputs.

While the  $\overline{OE}$  input is low, the eight outputs will be in a normal logic state (high or low logic level), and while high, the outputs will be in a high impedance state. The output control does not affect the internal operation of flip-flops. That is, the old data can be retained or the new data can be entered even while the outputs are off.

The three-state output configuration and the wide choice of outline will make its application in busorganized system simple. All inputs are equipped with protection circuits against static discharge and transient excess voltage. This integrated circuit has totally compatibility, input and output characteristic is with standard 54/74 LSTTL logic families.



October 1988

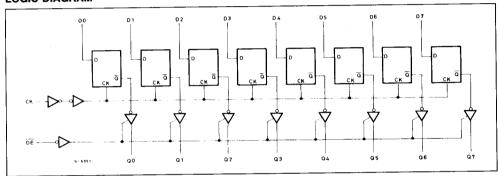
1/6

### **TRUTH TABLE**

	INPUTS	OUTPUTS			
ŌĒ	СК	D	Q		
Н	x	х	Z		
L	Ł	х	NO CHANGE		
L	<u>_</u>	L	L		
L	<u></u>	Н	Н		

X: DON'T CARE - Z: HIGH IMPEDANCE

### LOGIC DIAGRAM



### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit	
V <sub>CC</sub>	Supply Voltage	-0.5 to 7	V	
V <sub>I</sub>	DC Input Voltage	-0.5 to V <sub>CC</sub> +0.5	V	
Vo	DC Output Voltage	-0.5 to V <sub>CC</sub> +0.5	V	
lik	DC Input Diode Current	± 20	mA	
lok	DC Output Diode Current	± 20	mA	
lo	DC Output Source Sink Current Per Output Pin	± 35	mA	
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 70	mA	
PD	Power Dissipation	500 (*)	mW	
Tstg	Storage Temperature	- 65 to 150	°C	

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

(\*) 500 mW: ≅ 65°C derate to 300 mW by 10 mW/°C: 65°C to 85°C

2/6 SGS-THOMSON

### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit V	
V <sub>CC</sub>	Supply Voltage	4.5 to 5.5		
VI	Input Voltage	0 to V <sub>CC</sub>	V	
Vo	Output Voltage	0 to V <sub>CC</sub>	V	
TA	Operating Temperature 74HC Series 54HC Series	- 40 to 85 - 55 to 125	°C	
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	0 to 500	ns	

### DC SPECIFICATIONS

Symbol	Parameter	Vcc	Test Condition		T <sub>A</sub> =25°C 54HC and 74HC			40 to 85°C 74HC		– 55 to 125°C 54HC		Unit
					Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V <sub>IH</sub>	High Level Input Voltage	4.5 to 5.5			2.0			2.0	_	2.0	_	v
VIL	Low Level Input Voltage	4.5 to 5.5					0.8		0.8	_	0.8	v
VoH	High Level Output	4.5	V <sub>IN</sub>	Іон		4.5	_	4.4	_	4.4	_	
VOH Voltaç	Voltage		V <sub>IH</sub>	– 20 μA	4.4							v
			V <sub>IL</sub>	– 6.0 mA	4.18	4.31	_	4.13	<b>—</b>	4.10	_	
V <sub>OL</sub>	Low Level Output Voltage	4.5	V <sub>IN</sub>	l <sub>OL</sub>								
			V <sub>IH</sub> or	20 μΑ	_	0	0.1	_	0.1	_	0.1	v
			VIL	6.0 mA	_	0.17	0.26	_	0.33	_	0.40	
loz	3-State Output Off-State Current	5.5	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>OUT</sub> = V <sub>CC</sub> or GND			_	±0.5	_	±5.0	_	± 10.0	μΑ
I <sub>IN</sub>	Input Leakage Current	5.5	V <sub>IN</sub> = V <sub>CC</sub> or GND		_	_	±0.1	_	±1	_	±1	μΑ
Icc	Quiescent Supply		V <sub>I</sub> = V <sub>CC</sub> or GND  Per input: V <sub>IN</sub> = 0.5V or 2.4V  Other input: V <sub>CC</sub> or GND		_	_	4	_	40	_	80	μΑ
Icc	Current	5.5				_	2.0	_	2.9	_	3.0	mA

SGS-THOMSON MICROELECTROMICS

3/6

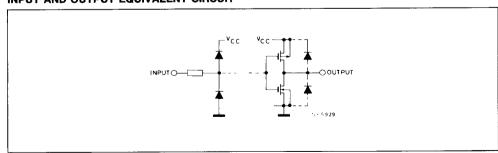
AC ELECTRICAL CHARACTERISTICS ( $C_L = 50pF$ , Input  $t_f = t_f = 6ns$ )

Symbol	Parameter	V <sub>CC</sub> Test Cond	Test Condition		A = 25° C and 7	= 25°C and 74HC		– 40 to 85°C 74HC		– 55 to 125°C 54HC	
				Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
t <sub>TLH</sub>	Output Transition Time	4.5		_	7	12	_	15		18	ns
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Time (CK-Q)	4.5		_	26	40	-	50	_	60	ns
fMAX	Maximum Clock Frequency	4.5		25	38	_	20	_	17	_	MHz
tw	Minimum Pulse Width	4.5		_	13	25	_	32		38	ns
t <sub>s</sub>	Minimum Set-up Time	4.5		_	6	15	_	19		23	ns
t <sub>h</sub>	Minimum hold Time	4.5		_	_	0	_	0		0	ns
t <sub>PZL</sub>	3-State Output Enable Time	4.5	$R_L = 1k\Omega$	_	27	42		53		63	ns
t <sub>PLZ</sub> t <sub>PHZ</sub>	3-State Output Disable Time	4.5	$R_L = 1k\Omega$	_	22	32		40	_	48	ns
CIN	Input Capacitance			_	5	10	_	10		10	pF
C <sub>OUT</sub>	Output Capacitance			-	10	_	_	_	_	_	pF
C <sub>PD</sub> (*)	Power Dissipation			_	60	_	-	_	-	-	pF

Note (\*) CPD is defined as the value of IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit)

Average opeating current is:  $I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$  (per FLIP/FLOP) And the  $C_{PD}$  when n circuits of FLIP/FLOP operate, can be gained by the following equation.  $C_{PD}$  (TOTAL) = 42 + 18 · n (pF)

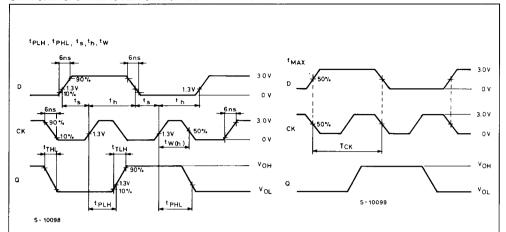
### INPUT AND OUTPUT EQUIVALENT CIRCUIT



4/6

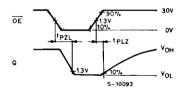
SGS-THOMSON MICROELECTRONICS

### SWITCHING CHARACTERISTICS TEST WAVEFORM



telz, tezl

The 1K $\Omega$  load resistors should be connected between outputs and V $_{CC}$  line and the 50pF load capacitors should be connected between outputs and GND line. All inputs except  $\overline{OE}$  input should be connected to V $_{CC}$  line or GND line such that outputs will be in low logic level while  $\overline{OE}$  input is held low.



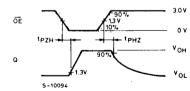
Duty cycle of CK: 50%

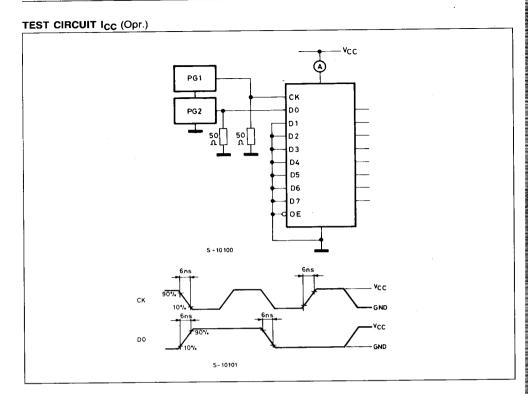
$$f_{MAX} = \frac{1}{T_{CK}}$$

tenz, tezh

The  $1K\Omega$  load resistors and the 50pF load capacitors should be connected between each output and GND line.

All inputs except  $\overline{OE}$  input should be connected to  $V_{CC}$  or GND line such that output will be in high logic level while  $\overline{OE}$  inputs is held low.





560

SGS-THOMSON MICROELECTRONICS